

Silicon PNP transistor epitaxial type AP964

[Applications]

High voltage switching and amplifier

[Feature]

High voltage $V_{CEO} = -400V$

Small collector output capacitance $C_{ob} = 2.5pF$ (Typ.) at $V_{CB} = -20V$

NPN complementary pair with CP964

[Absolute maximum ratings ($T_a = 25C$)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	V_{CBO}	-400	V
Collector-emitter voltage	V_{CEO}	-400	V
Emitter-base voltage	V_{EBO}	-7	V
Collector current	I_C	-300	mA
Junction temperature	T_j	150	C
Storage temperature	T_{stg}	-55 to 150	C

[Electrical characteristics ($T_a = 25C$)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-400	-	-	V	$I_C = -100\mu A, I_E = 0A$
Collector-emitter breakdown voltage	BV_{CEO}	-400	-	-	V	$I_C = -1mA, I_B = 0A$
Emitter-base breakdown voltage	BV_{EBO}	-7	-	-	V	$I_E = -100\mu A, I_C = 0A$
Collector cut-off current	I_{CBO}	-	-	-0.5	μA	$V_{CB} = -400V, I_E = 0A$
DC current gain 1	h_{FE1}	40	-	-	-	$V_{CE} = -10V, I_C = -4mA$
DC current gain 2	h_{FE2}	70	-	200	-	$V_{CE} = -10V, I_C = -20mA$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_C = -50mA, I_B = -5mA$
Base-emitter saturation voltage	$V_{BE(sat)}$	-	-	-1.1	V	$I_C = -50mA, I_B = -5mA$
Transition frequency	f_T	50	-	-	MHz	$V_{CE} = -10V, I_E = 20mA$
Collector output capacitance	C_{ob}	-	-	7	pF	$V_{CB} = -20V, f = 1MHz, I_E = 0A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

